

Please amend lines 1 to 10 as follows:

--Field of the Invention--

Please amend the second paragraph beginning on page 12 and ending on page 13 as follows:

--For example, in this 3-5 group compound semiconductor, a light emitting layer, n-type layer, low carrier concentration layer and p-type layer are adjacent in this order. For efficient recombination and light emission of injected charges, it is preferable that the band gap of an n-type layer is larger than that of a light emitting layer. The band gap between an n-type layer and a light emitting layer is preferably 0.1 eV or more, more preferably 0.3 eV or more. The preferable film thickness of an n-type layer is 10 Å or more and 1 μm or less. The light emitting efficiency of a light emitting device may decrease both when the film thickness of a low carrier concentration layer is lower than 1 Å and when larger than 1 μm. Therefore, the preferable film thickness of a low carrier concentration layer is 1 Å or more and 1 μm or less. The light emitting efficiency of a light emitting device may decrease both